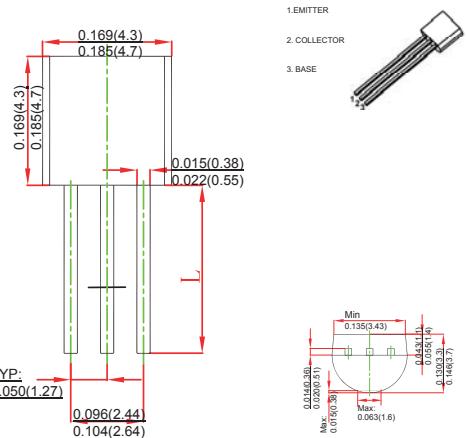


**TO-92 Plastic-Encapsulate Transistors**
**FEATURES**

- General Purpose Application Switching Application
- TRANSISTOR (PNP)

**MECHANICAL DATA**

- Case style: TO-92 molded plastic
- Mounting position: any

**TO-92**

**MAXIMUM RATINGS AND CHARACTERISTICS**

@ 25°C Ambient Temperature (unless otherwise noted)

Symbol	Parameter	Value	Unit
$V_{CBO}$	Collector-Base Voltage	-35	V
$V_{CEO}$	Collector-Emitter Voltage	-30	V
$V_{EBO}$	Emitter-Base Voltage	-5	V
$I_c$	Collector Current -Continuous	-500	mA
$P_c$	Collector Power Dissipation	500	mW
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient	250	°C /W
$T_j$	Junction Temperature	150	°C
$T_{stg}$	Storage Temperature	-55 ~ +150	°C

**ELECTRICAL CHARACTERISTICS** Ta = 25°C unless otherwise specified

Parameter	Symbol	Test conditions	Min	Typ	
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -100\mu A, I_E = 0$	-35		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1mA, I_B = 0$	-30		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -100\mu A, I_C = 0$	-5		V
Collector cut-off current	$I_{CBO}$	$V_{CB} = -35 V, I_E = 0$		-0.1	μA
Emitter cut-off current	$I_{EBO}$	$V_{EB} = -5 V, I_C = 0$		-0.1	μA
DC current gain	$h_{FE1}$	$V_{CE} = -1 V, I_C = -100mA$	70	240	
	$h_{FE2}$	$V_{CE} = -6 V, I_C = -400mA$	25		
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -100mA, I_B = -10mA$		-0.25	V
Base-emitter voltage	$V_{BE(on)}$	$V_{CE} = -1V, I_C = -100mA$		-1	V
Transition frequency	$f_T$	$V_{CE} = -6 V, I_C = -20mA$ $f = 100MHz$		200	MHz
Collector output capacitance	$C_{ob}$	$V_{CB} = -6V, I_E = 0, f = 1MHz$		13	pF

**CLASSIFICATION OF  $h_{FE}$** 

Rank	O	Y
Range	$h_{FE(1)}$	70-140
	$h_{FE(2)}$	25(min)
		120-240
		40(min)